



Low dimension nano-systems: features and applications

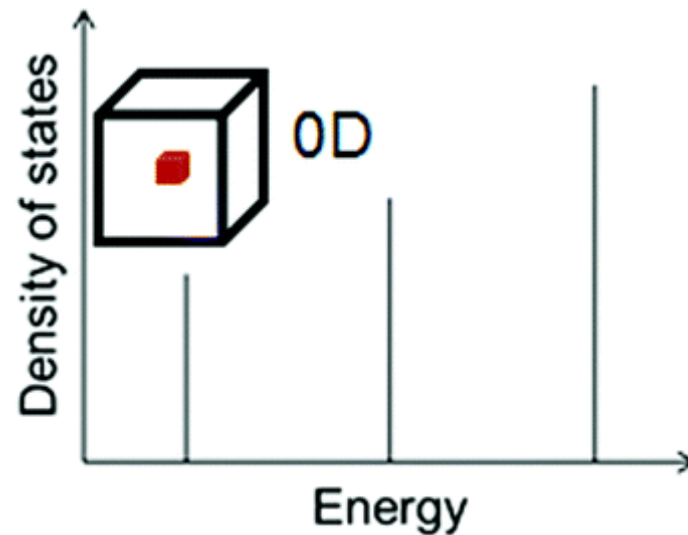
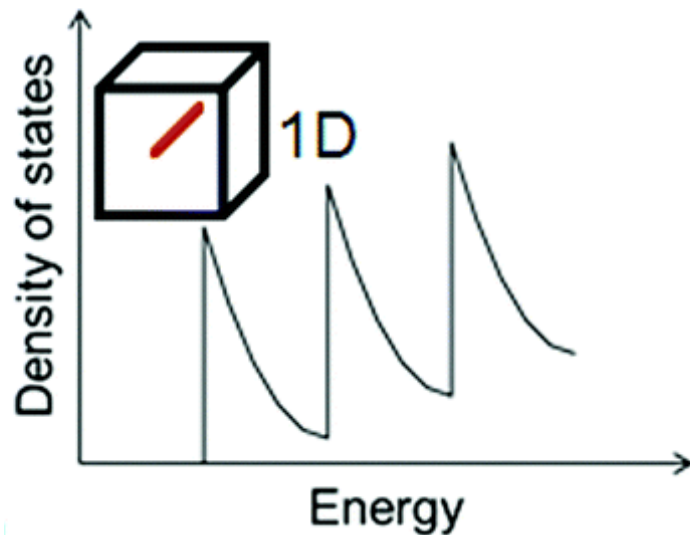
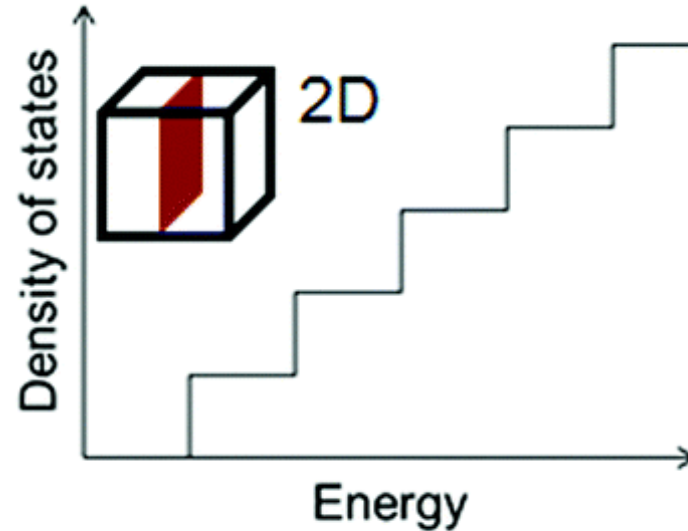
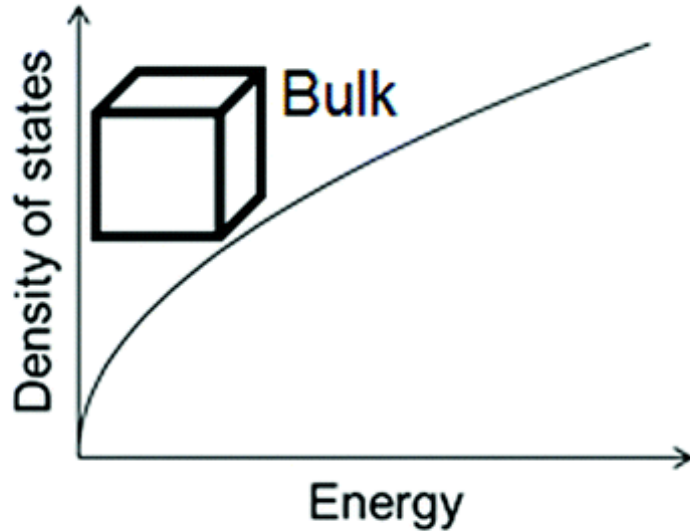
Claudio Puglia

First year Ph.D. seminar

Outline

- What are low dimensional nano-systems?
 - Fabrication
 - Applications
- Conclusions and Q&A

Low dimensional nano-systems



Lower D

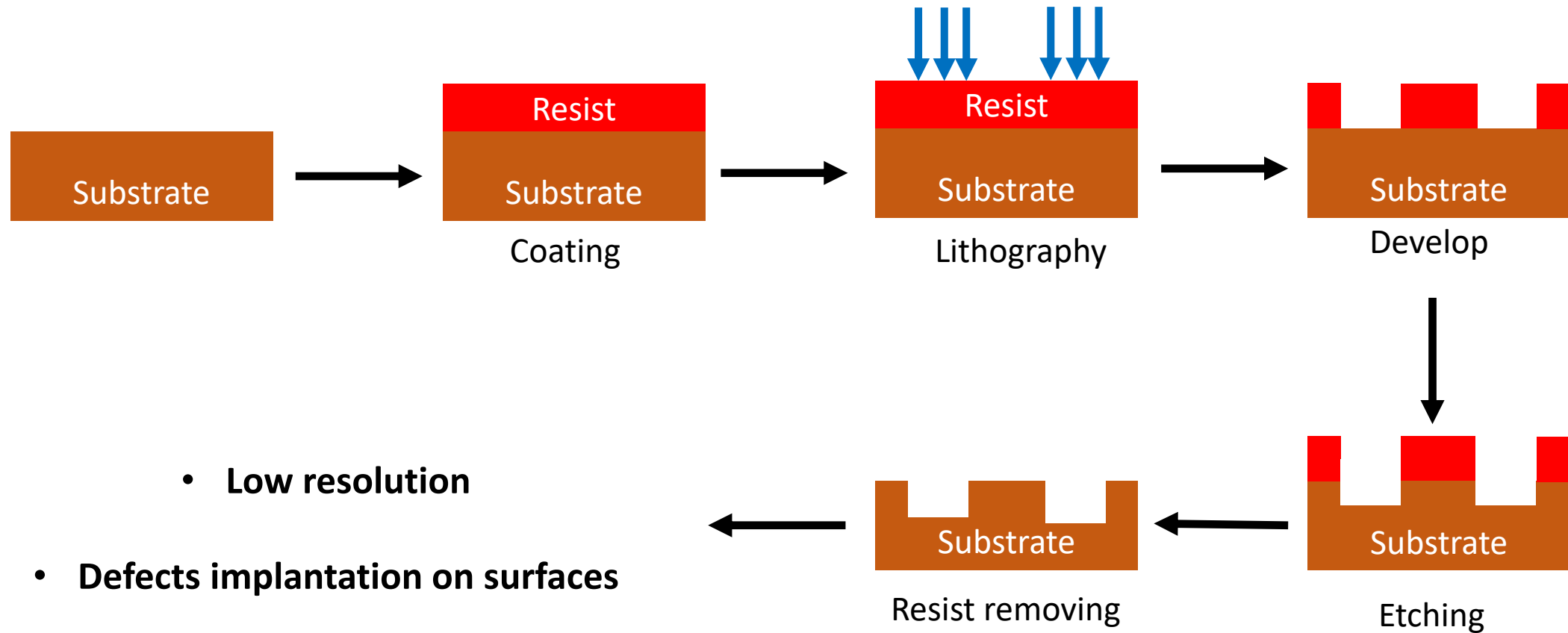


Sharper D.o.S.



Potential advantage
for optical and
electronic devices

Fabrication: Top-Down method



- **Low resolution**
- **Defects implantation on surfaces**

Etching

Wet

The sample is immersed in an aqueous solution which selectively dissolves the substrate but not the mask (es: KOH for Si, HF for SiO₂, etc.)



Simple, versatile, cheap, isotropic, ...



Isotropic, capillary forces when drying, mask adhesion issues...

Dry

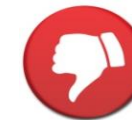
RIE (Reactive Ion Etching)

ICP (Inductively Coupled Plasma)

Reactive gases (usually ionized) selectively dissolve the substrate but not the mask with a combination of chemical and physical factors (es: CF₄)



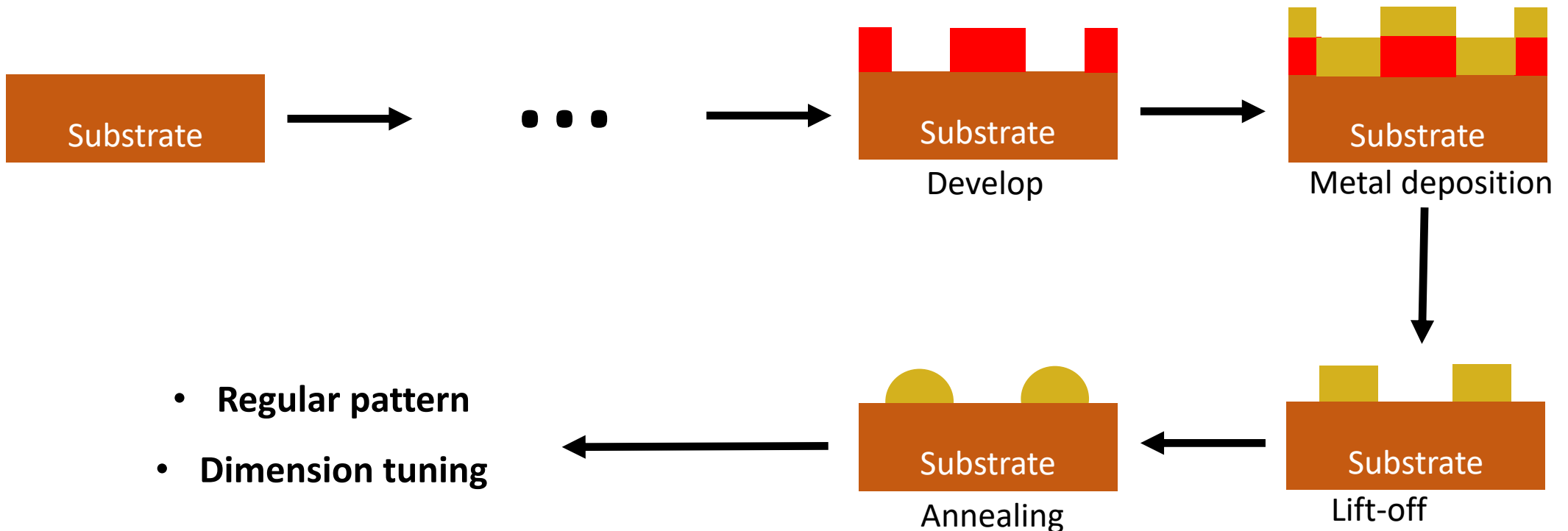
Directional, no capillary forces, very suited to certain material combinations



Requires complex (expensive!) facilities, and dangerous gases

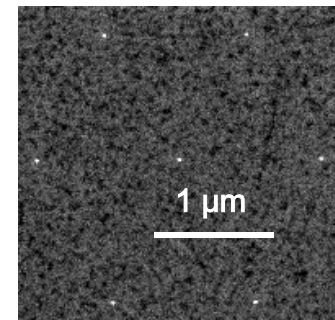
Fabrication: Bottom-Up method

*Vapor-Liquid-Solid (VLS) growth occurs when an alloy droplet starting from a **metal catalyst** becomes supersaturated with material from a gaseous reactant. The material then precipitates from the solid-liquid interface to form a nanowire.*



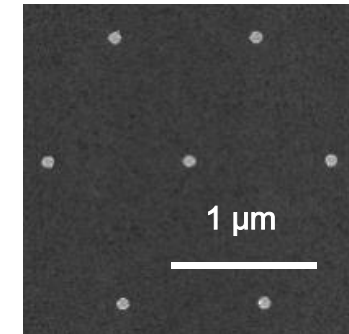
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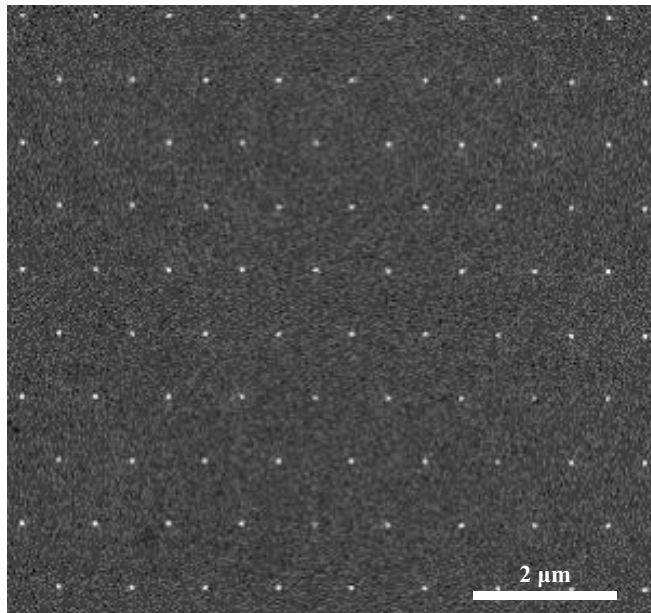


10nm

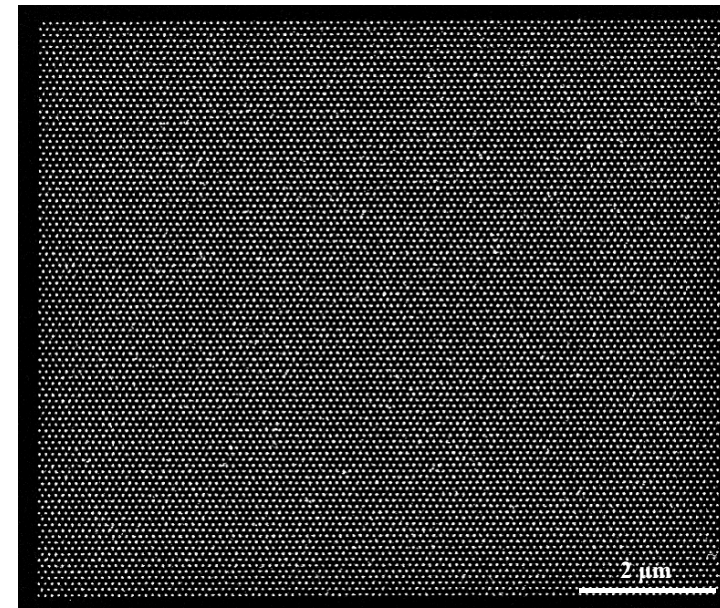
Diameter



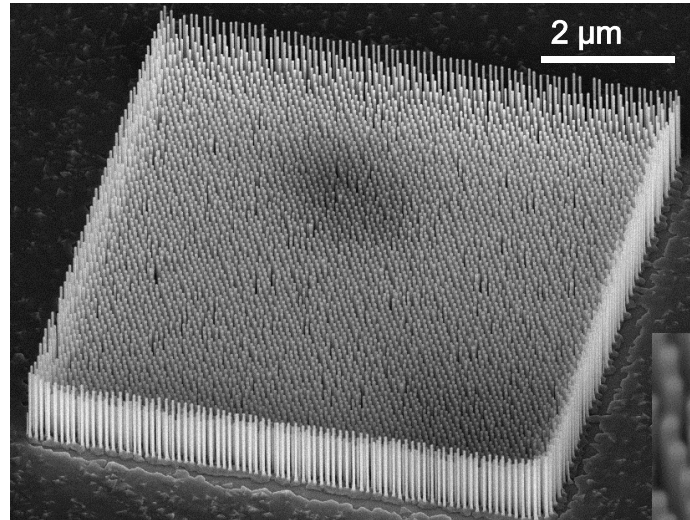
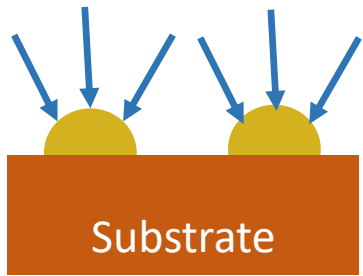
80nm



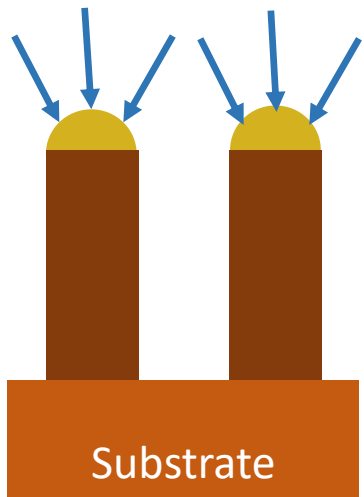
Density



Fabrication: Bottom-Up method

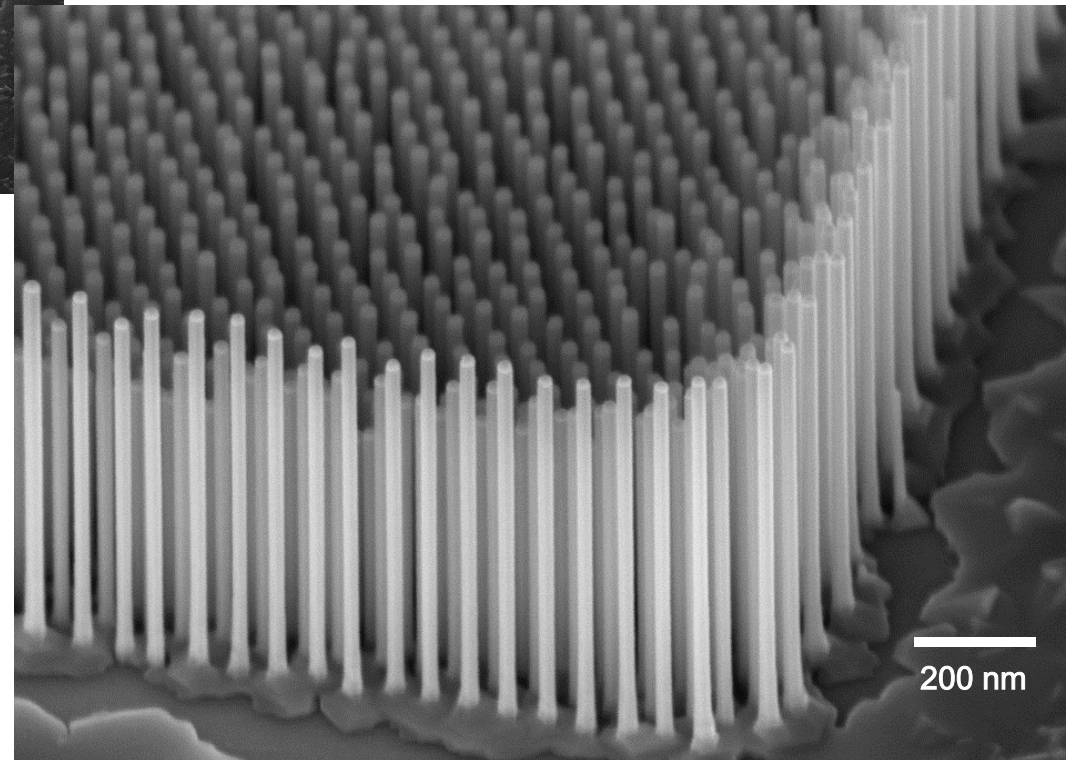


Center-to-center distance 100nm



Pitch = 100 nm

Density = 115 μm⁻²



Fabrication: Bottom-Up method

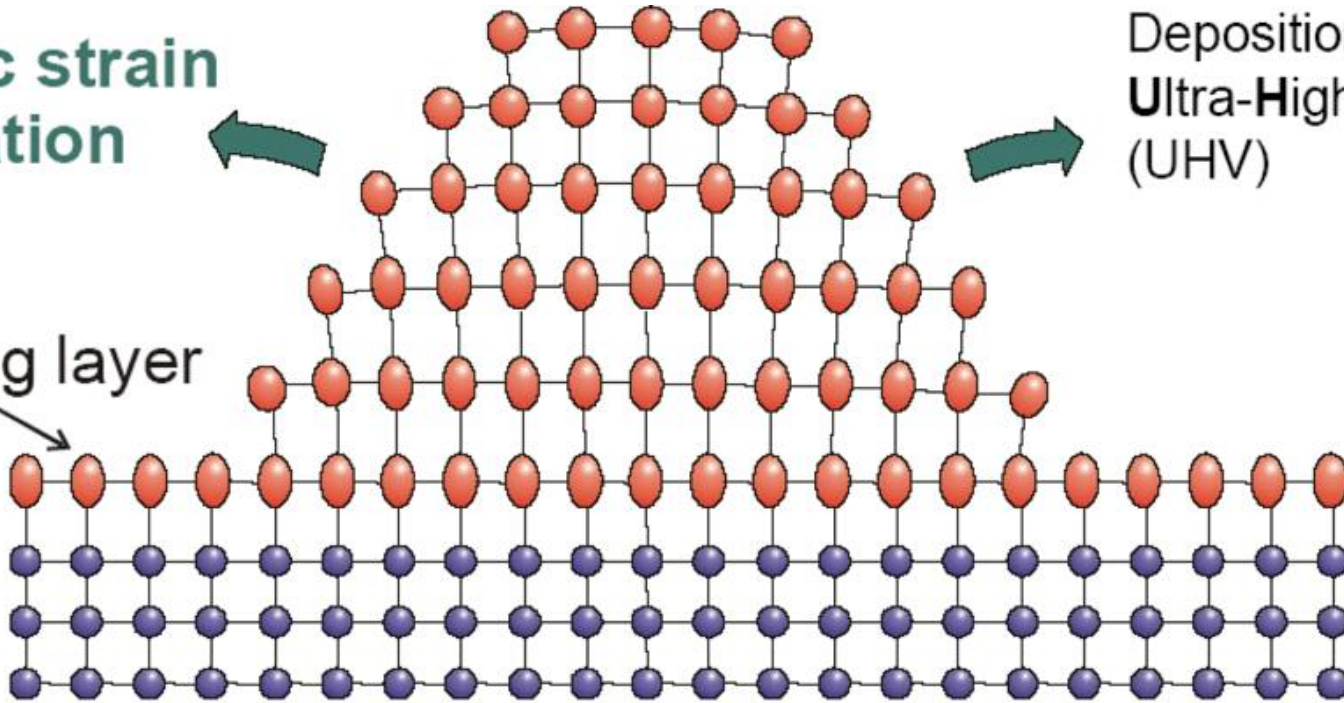
elastic strain relaxation



Deposition in
Ultra-High-Vacuum
(UHV)



wetting layer



**No control over
position and
dimension**

Stranski Krastanov growth



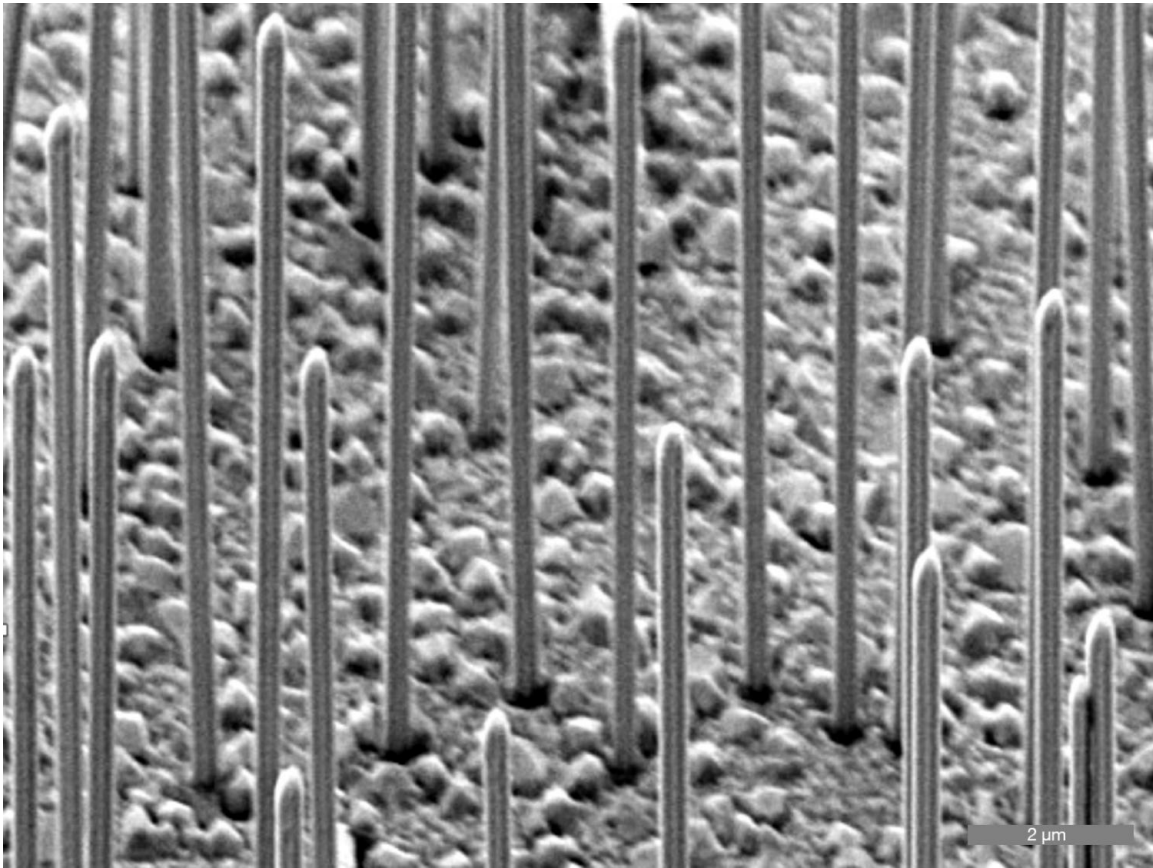
smaller lattice constant,
large band gap
e.g.: Si, GaAs, GaInP



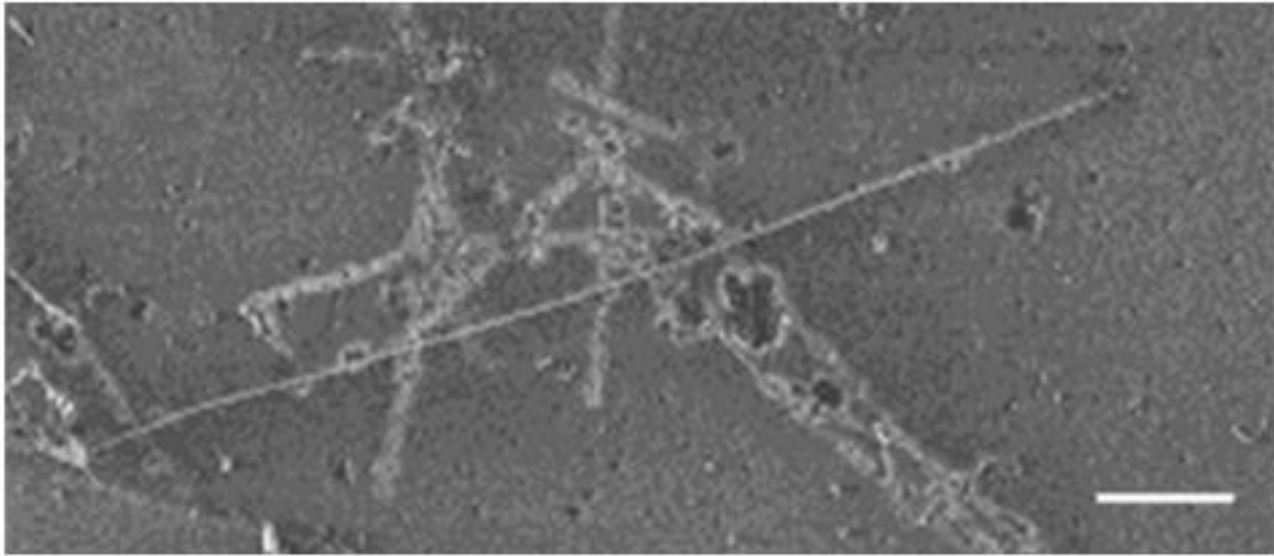
larger lattice constant,
smaller band gap
e.g.: Ge, InAs, InP

Quantum nanoWiRe (QWR)

- **Investigation of 1D system properties**
 - **Photo electric applications**
 - **Transport properties**
 - **Extension of Moore's law**

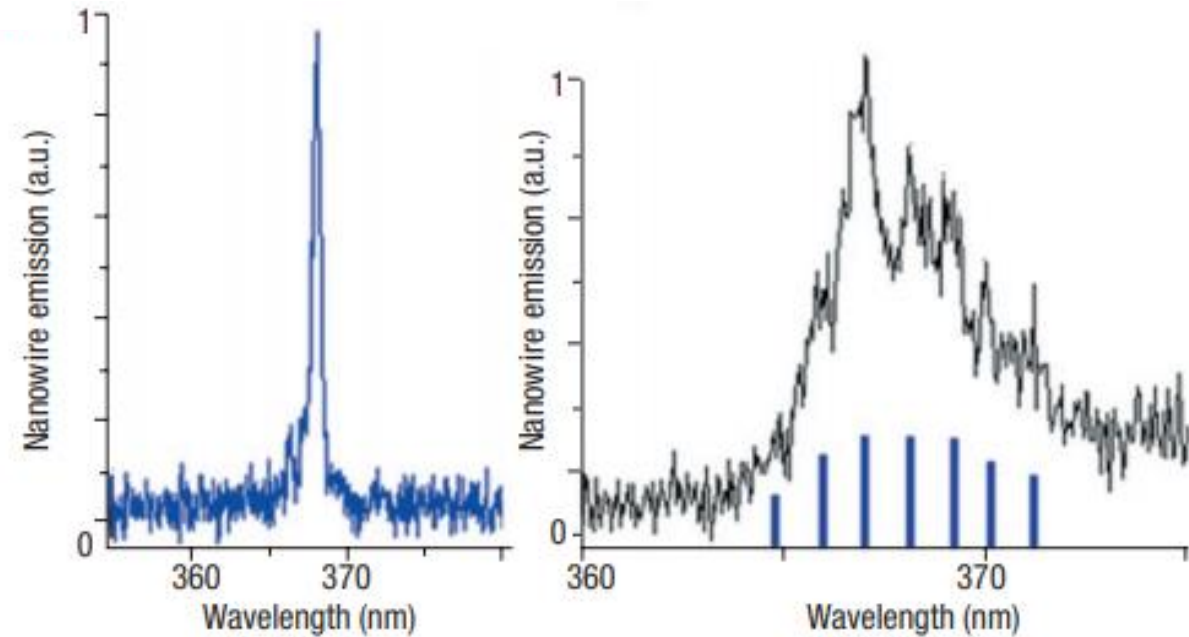


Nanowire application: Laser



Optical pumping with a far infrared pulsed laser (OPA 1170-1600nm)

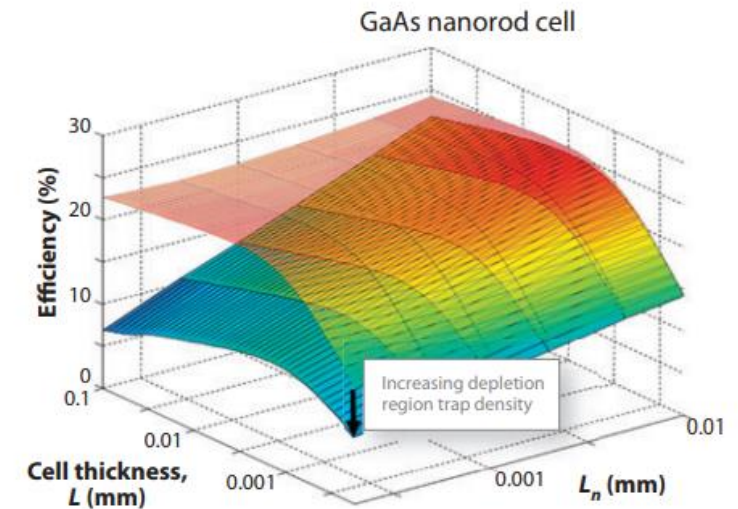
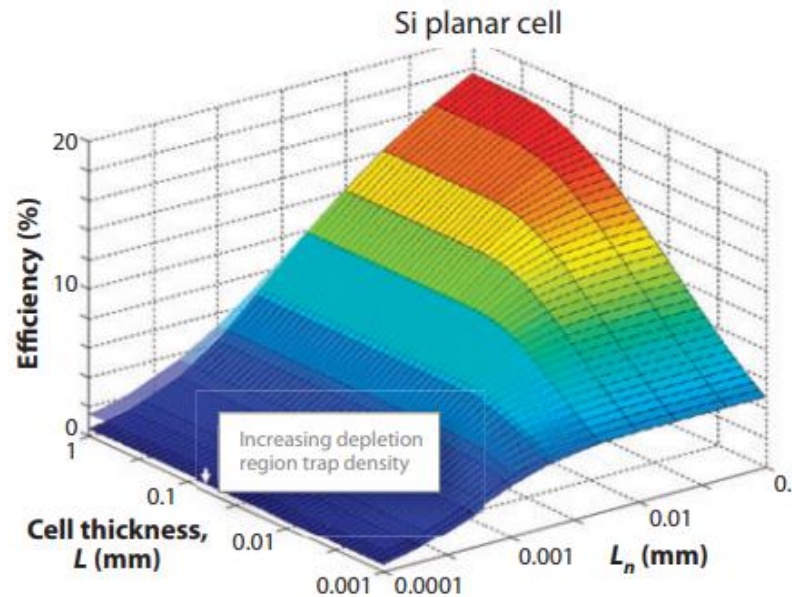
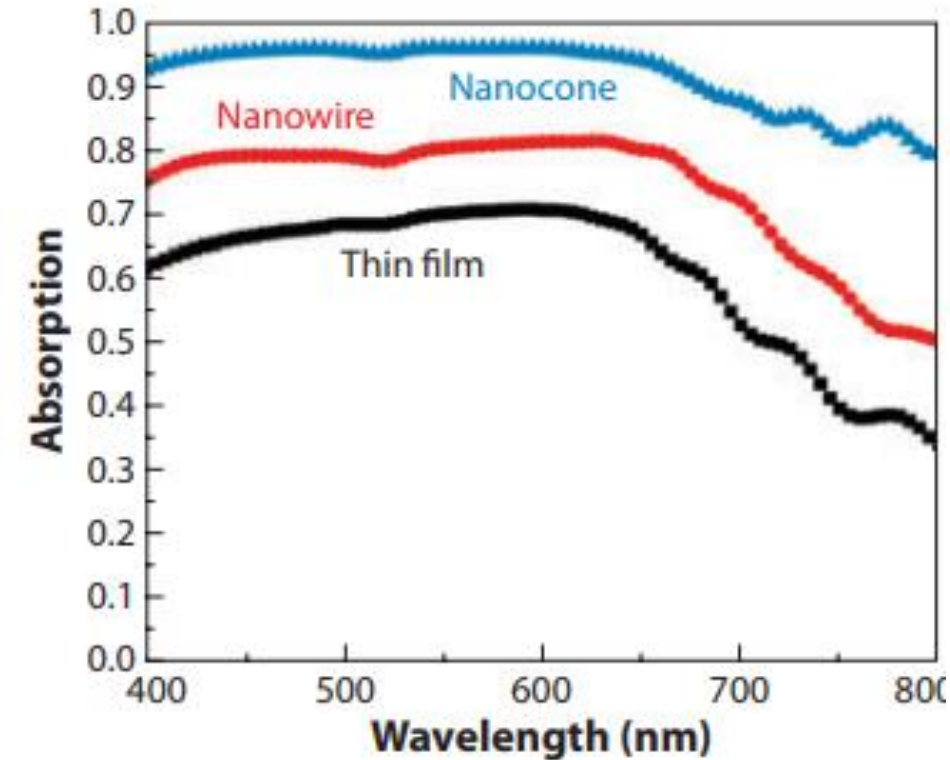
GaN nanowires from VLS technique



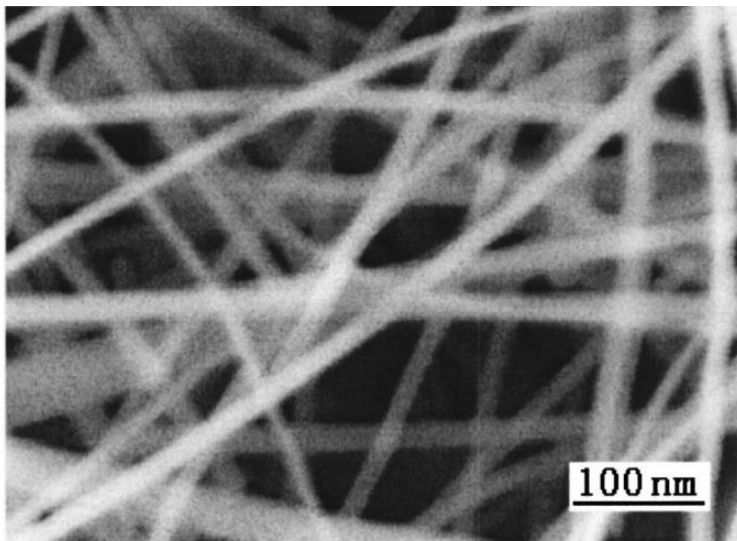
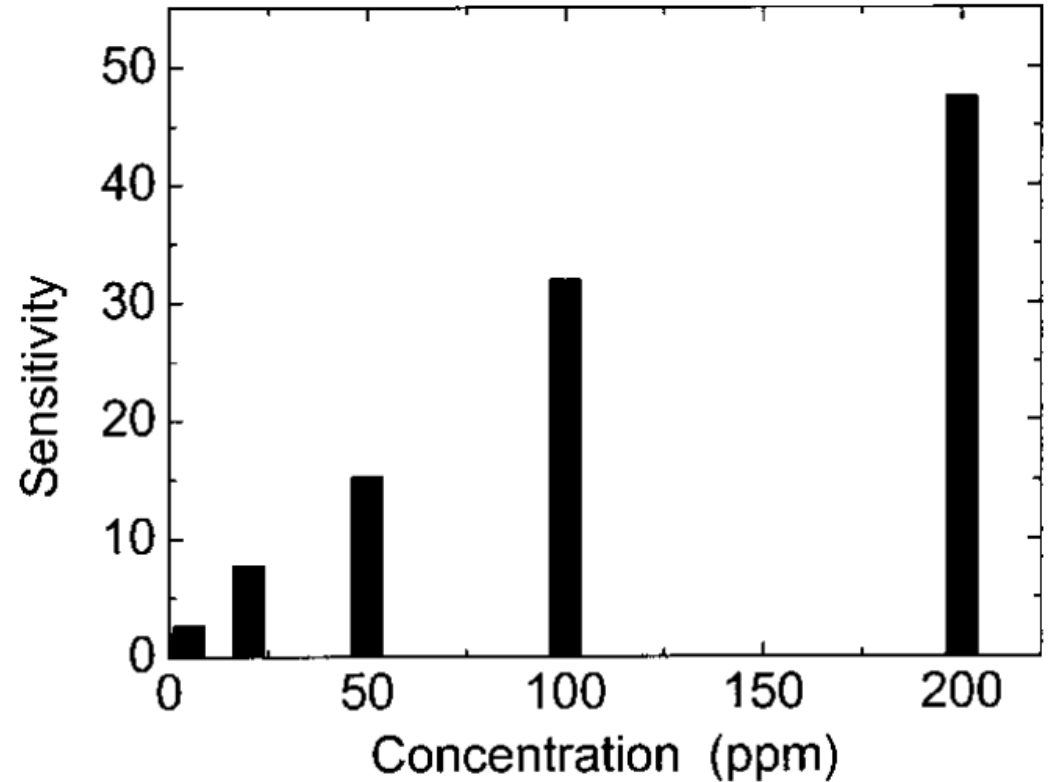
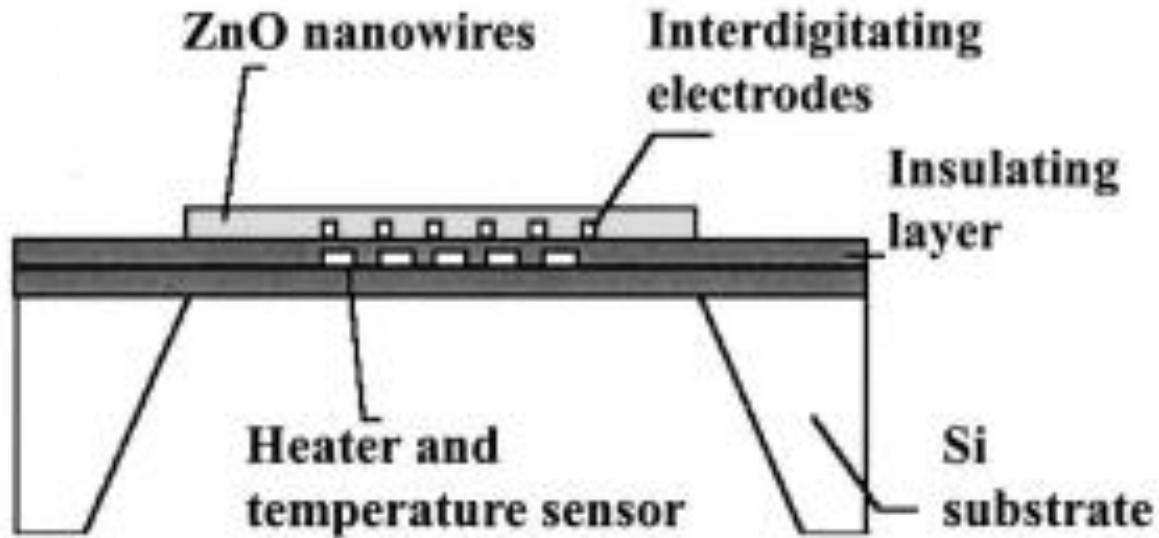
J. C. Johnson, et al. Nature Mater. 1, 106 (2002).

Nanowire application: Solar Cell

- Higher absorption
- Potentially less cost
- Not yet scalable

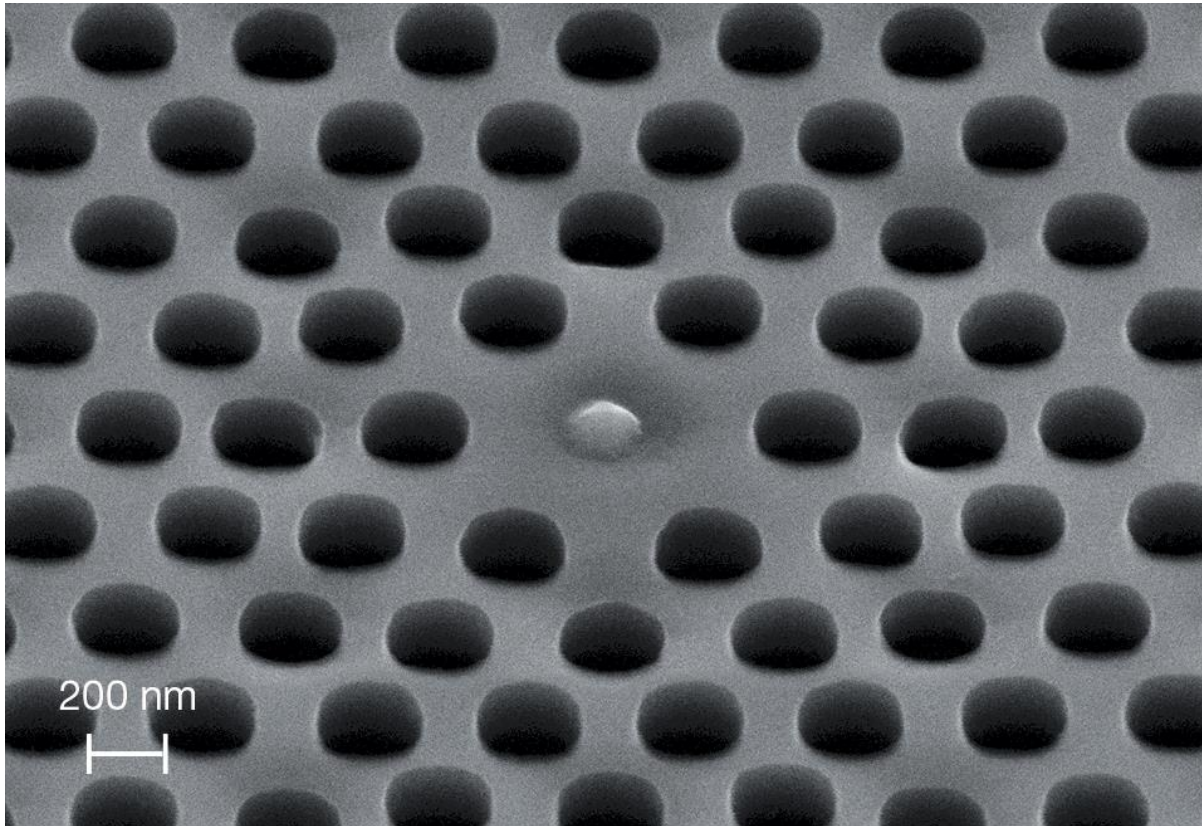


Nanowire application: Ethanol sensor



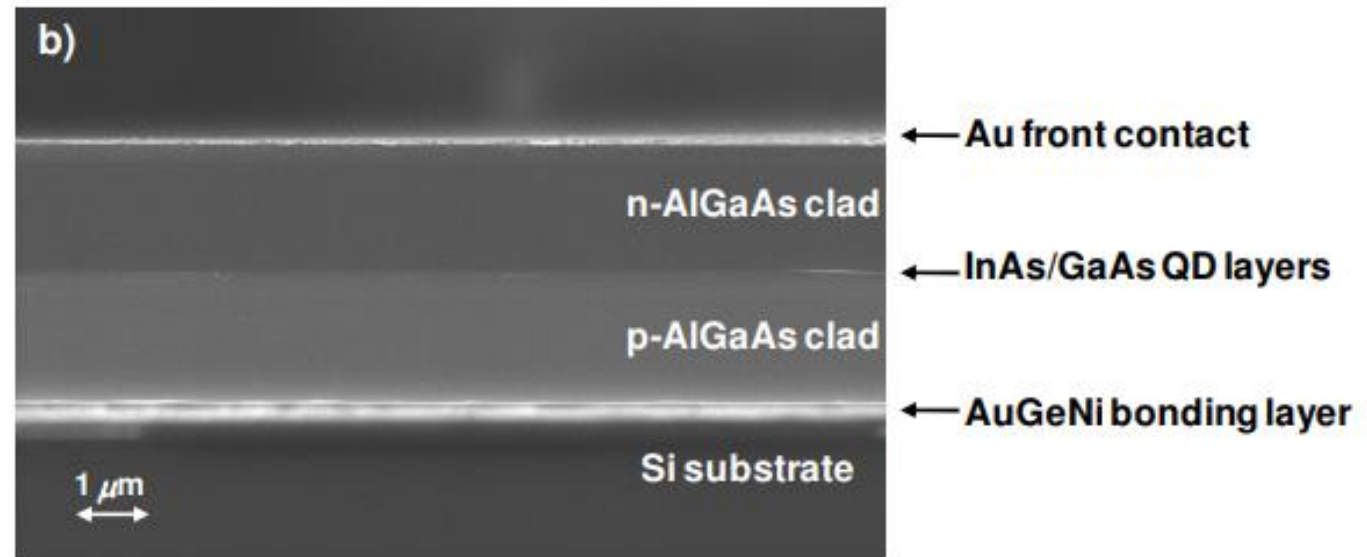
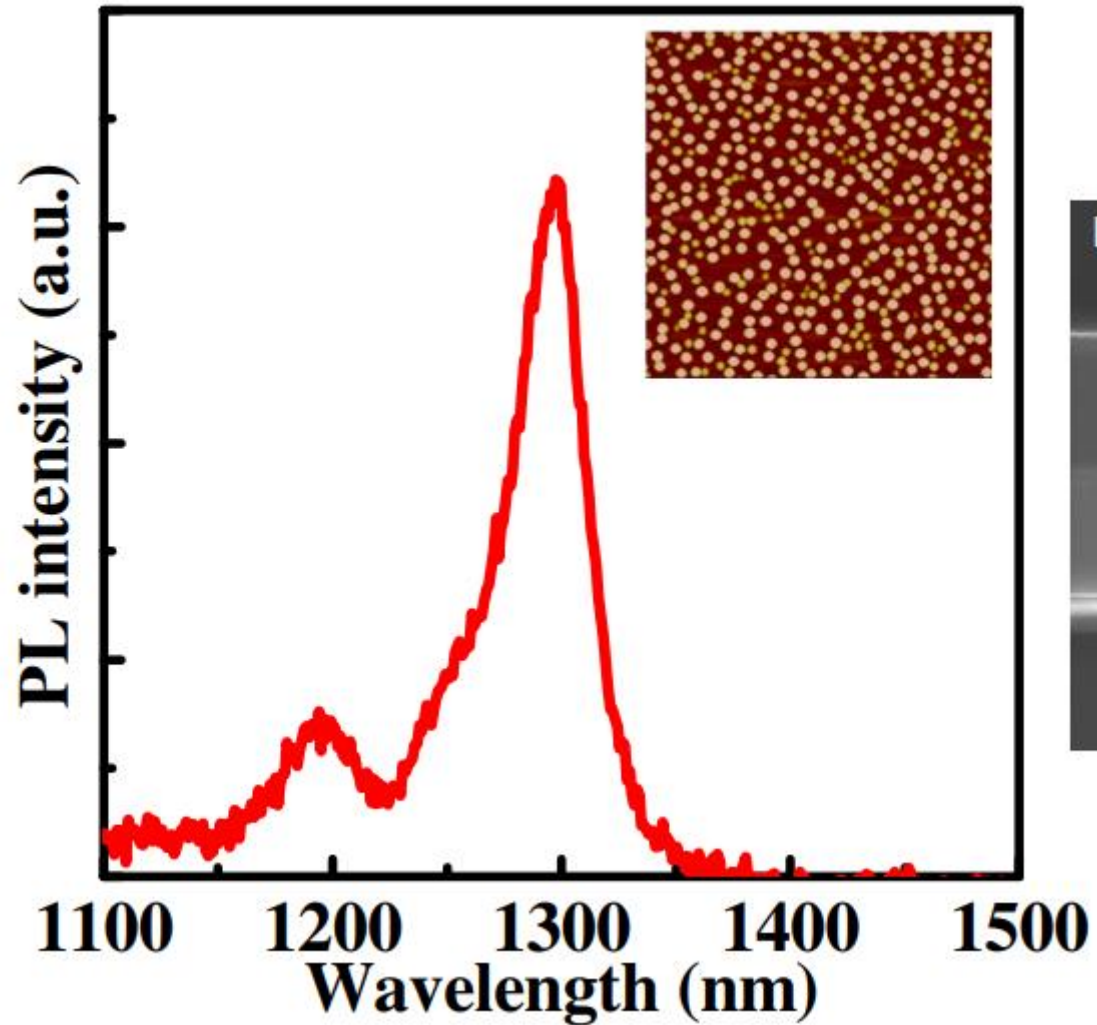
Fabrication and ethanol sensing characteristics of ZnO nanowire gas sensors
Appl. Phys. Lett. 84, 3654 (2004)

Quantum Dot (QD)

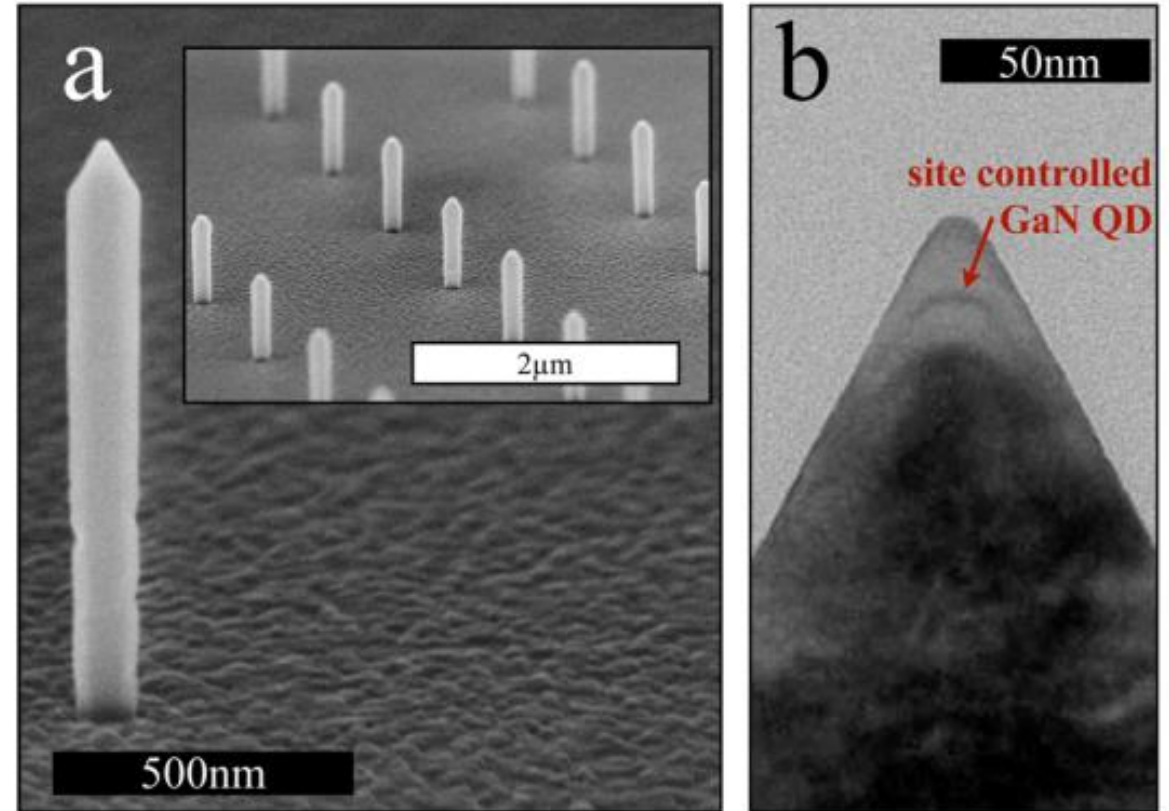
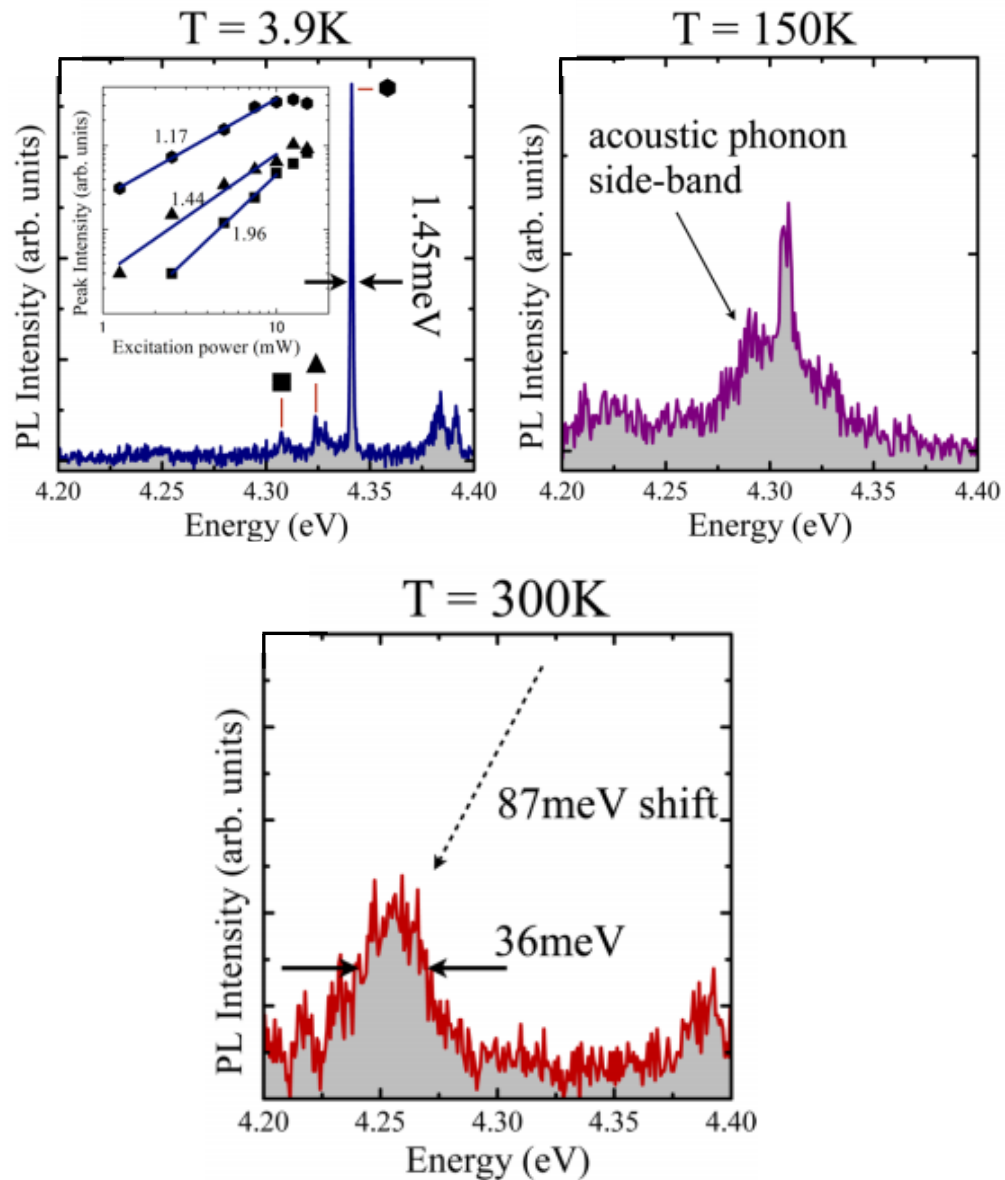


- A quantum dot is a zero-dimensional object in which electrons are confined in all three dimensions.
- Confinement leads to improved performance of advanced optoelectronic devices (lasers, ...)
 - Applications also in quantum information technology
- Quantum dots can be obtained by strain-driven self-assembly (Stranski-Krastanov growth mode)

Quantum Dot application: Laser



Quantum Dot application: Single Photon source



Senellart, P., et al.. (2017). High-performance semiconductor quantum-dot single-photon sources. *Nature Nanotechnology*, 12(11), 1026–1039.

Conclusions

Nanowires

1. Well developed fabrication techniques
2. Mid-term commercial applications
3. Sensor-friendly technology

Quantum Dot

1. Less controllable fabrication process
2. Possible High Output power laser
3. Quantum communication applications